

High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

$$I_{TAV} = 15\text{ A}$$

$$V_T = 1.35\text{ V}$$

Three Quadrants operation: QI - QIII
 1~ Triac

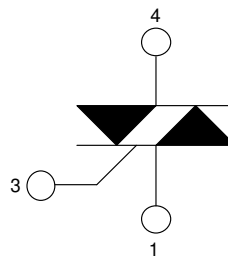
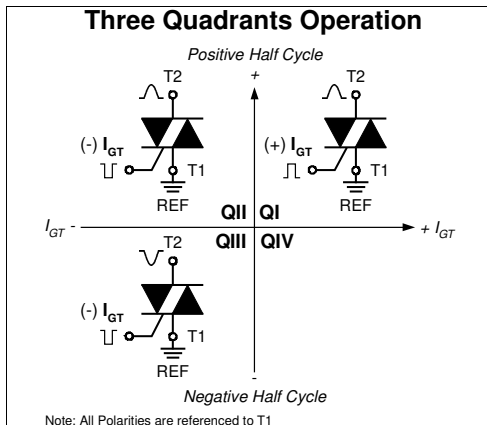
Part number

CLA30MT1200NPZ

Marking on Product: CLA30MT1200NPZ



Backside: anode/cathode



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

Disclaimer Notice

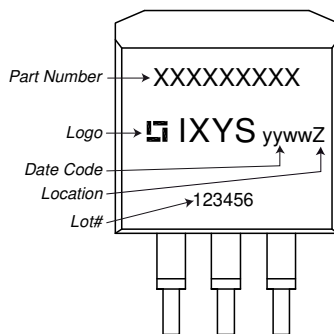
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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		10	μA	
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		1.5	mA	
V_T	forward voltage drop	$I_T = 15 A$	$T_{VJ} = 25^{\circ}C$		1.35	V	
		$I_T = 30 A$			1.68	V	
		$I_T = 15 A$	$T_{VJ} = 125^{\circ}C$		1.35	V	
		$I_T = 30 A$			1.79	V	
I_{TAV}	average forward current	$T_C = 120^{\circ}C$	$T_{VJ} = 150^{\circ}C$		15	A	
I_{RMS}	RMS forward current per phase	180° sine			33	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.89	V	
r_T	slope resistance				30	m Ω	
R_{thJC}	thermal resistance junction to case				0.95	K/W	
R_{thCH}	thermal resistance case to heatsink			0.3		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		130	W	
I_{TSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		170	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		185	A	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		145	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		155	A	
I^2t	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		145	A ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		140	A ² s	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		105	A ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		100	A ² s	
C_J	junction capacitance	$V_R = 400 V \quad f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		9	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		5	W	
		$t_p = 300 \mu s$			1	W	
P_{GAV}	average gate power dissipation				0.2	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 Hz$ repetitive, $I_T = 45 A$			150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.3 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 15 A$			500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs	
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.3	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		± 40	mA	
			$T_{VJ} = -40^{\circ}C$		± 60	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V	
I_{GD}	gate non-trigger current				± 1	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		70	mA	
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$					
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		50	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$					
t_q	turn-off time	$V_R = 100 V; I_T = 15 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	μs	

Package TO-263 (D2Pak-HV)		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/Apb}$		terminal to backside	4.7			mm

Product Marking



Part description

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200V)
 30 = Current Rating [A]
 MT = 1~ Triac
 1200 = Reverse Voltage [V]
 N = Three Quadrants operation: QI - QIII
 PZ = TO-263AB (D2Pak) (2HV)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA30MT1200NPZ-TRL	CLA30MT1200NPZ	Tape & Reel	800	516960
Alternative	CLA30MT1200NPZ-TUB	CLA30MT1200NPZ	Tube	50	525255

Similar Part	Package	Voltage class
CLA30MT1200NPB	TO-220AB (3)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

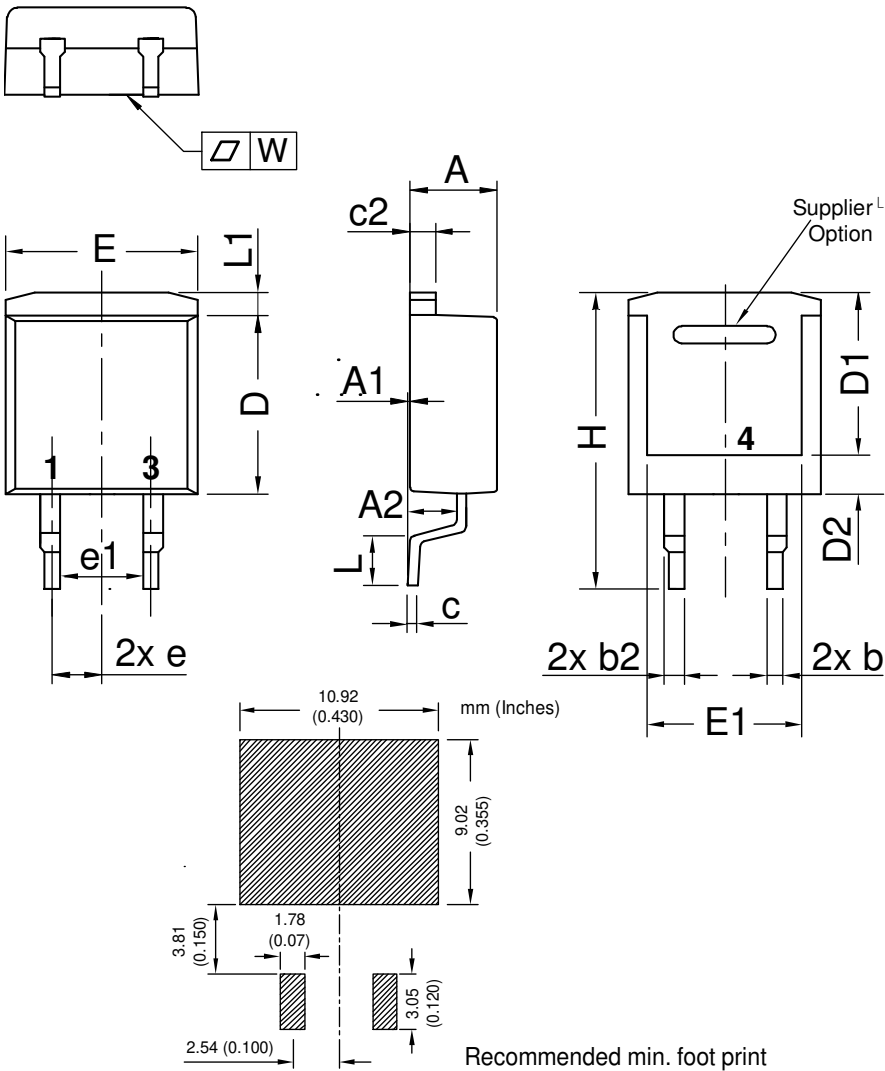


Thyristor

$V_{0\ max}$	threshold voltage	0.89	V
$R_{0\ max}$	slope resistance *	27	mΩ

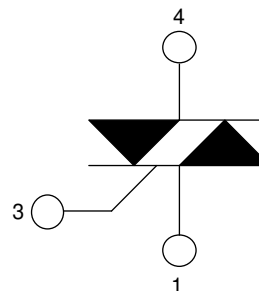


Outlines TO-263 (D2Pak-HV)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



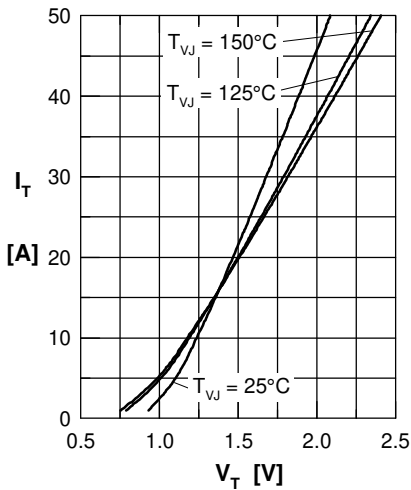
Thyristor


Fig. 1 Forward characteristics

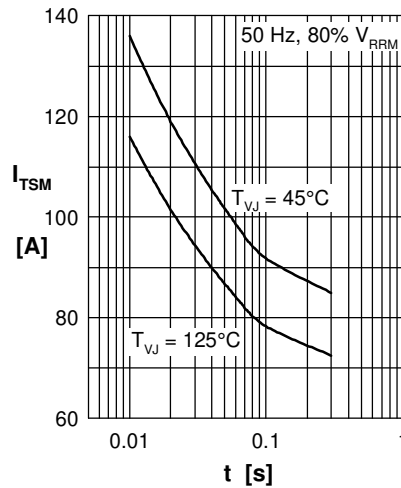


Fig. 2 Surge overload current

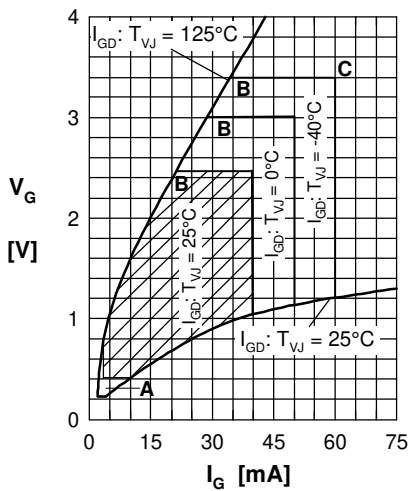

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics



Fig. 5 Gate controlled delay time



Fig. 6 Max. forward current at case temperature

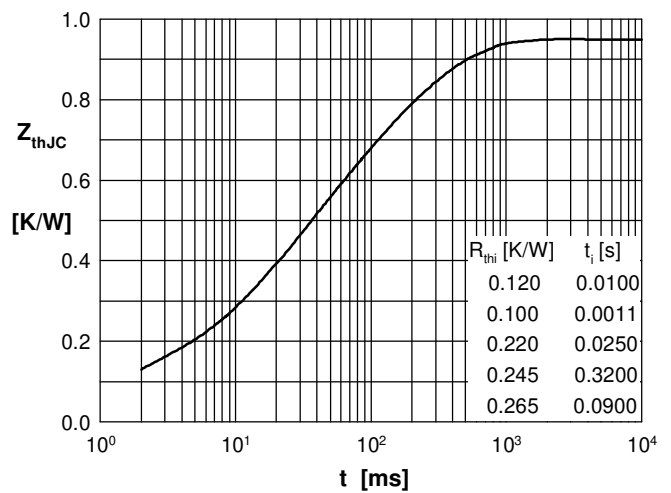

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance